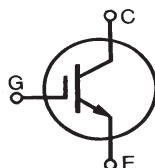


GenX3™ 600V IGBTs

IXGK320N60B3 IXGX320N60B3

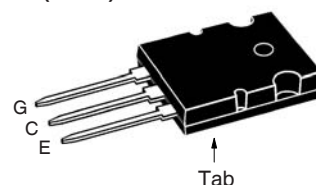
$$\begin{aligned} V_{CES} &= 600V \\ I_{C90} &= 320A \\ V_{CE(sat)} &\leq 1.6V \end{aligned}$$

Medium-Speed Low-Vsat PT
IGBTs for 5-40 kHz Switching

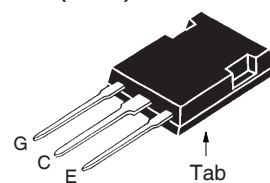


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	500	A
I_{C90}	$T_C = 90^\circ\text{C}$	320	A
I_{LRMS}	Terminal Current Limit	160	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	1200	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 320$ $V_{CE} \leq V_{CES}$	A V
P_C	$T_C = 25^\circ\text{C}$	1700	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ\text{C}$
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXGX)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247 (IXGX)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for Low Conduction and Switching Losses
- High Current Capability
- Square RBSOA

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 4mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			75 μA 2 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 400 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $I_C = 320A$		1.4 2.0	1.6 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	70	125	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		18	nF
C_{oes}			960	pF
C_{res}			130	pF
Q_g	$I_C = 320\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		585	nC
Q_{ge}			105	nC
Q_{gc}			215	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$		44	ns
t_{ri}			66	ns
E_{on}			2.7	mJ
$t_{d(off)}$			250	ns
t_{fi}			165	ns
E_{off}			3.5	5.0 mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$		40	ns
t_{ri}			67	ns
E_{on}			3.5	mJ
$t_{d(off)}$			330	ns
t_{fi}			265	ns
E_{off}			5.4	mJ
R_{thJC}			0.15	0.073°C/W
R_{thCS}				$^\circ\text{C/W}$

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

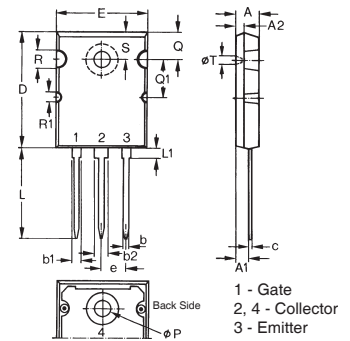
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

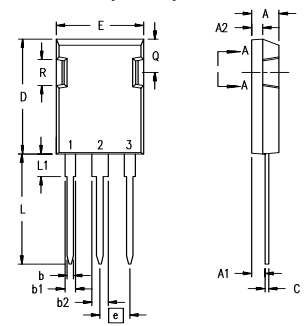
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 AA (IXGK) Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ (IXGX) Outline



Terminals: 1 - Gate
2 - Collector
3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

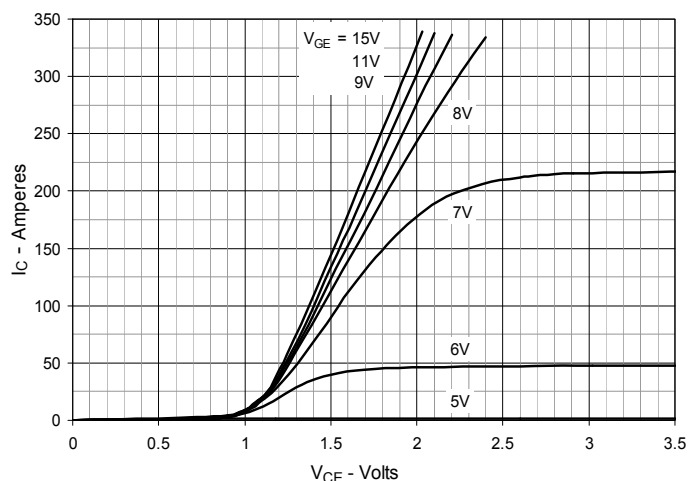


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

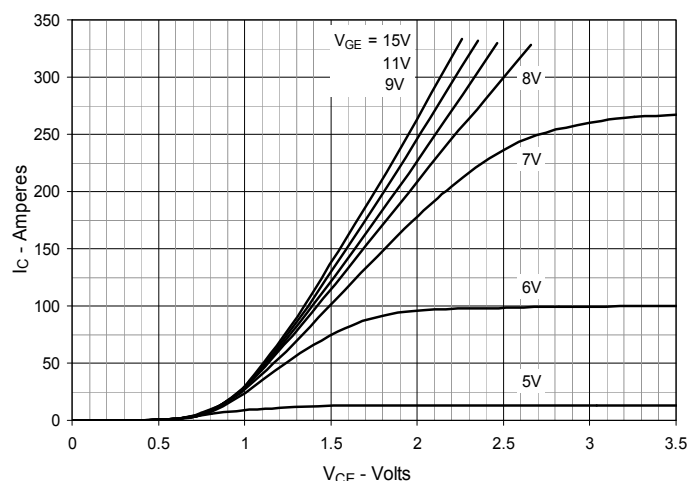


Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

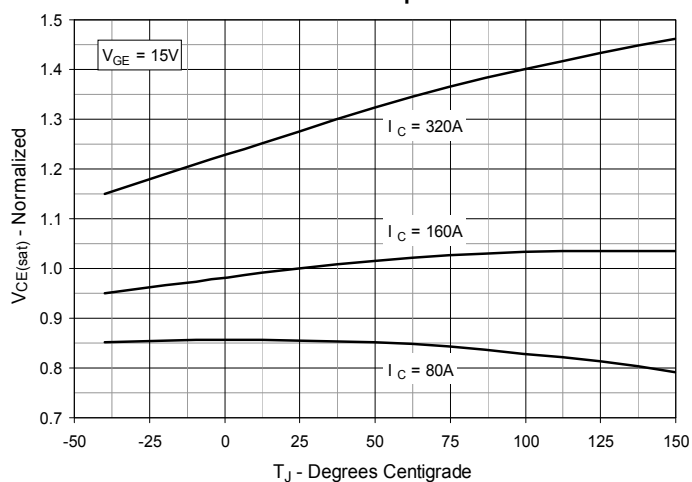


Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

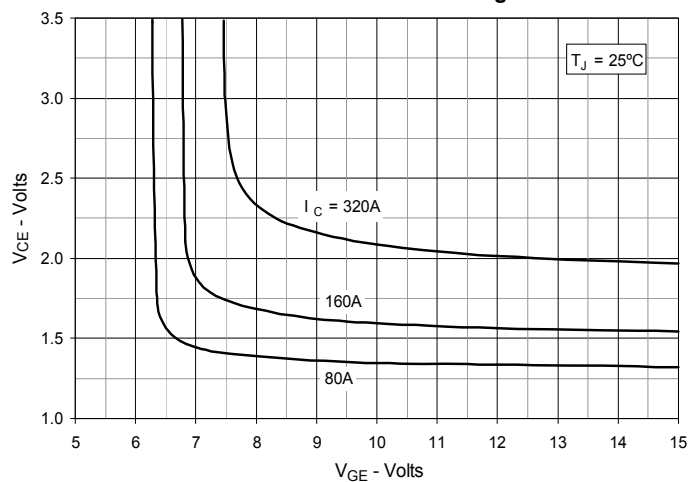


Fig. 5. Input Admittance

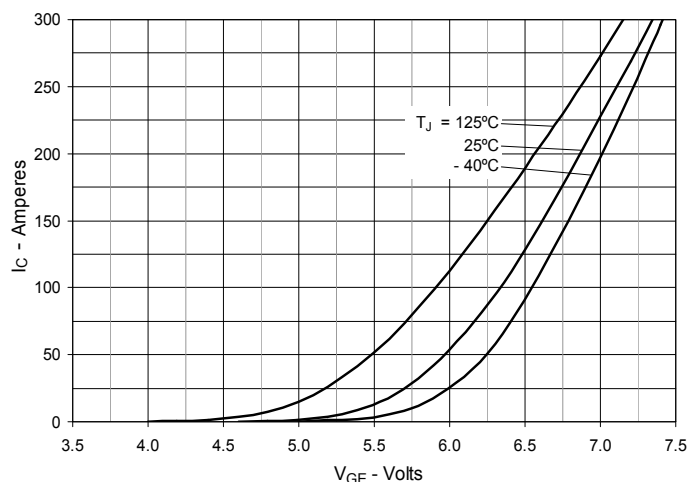


Fig. 6. Transconductance

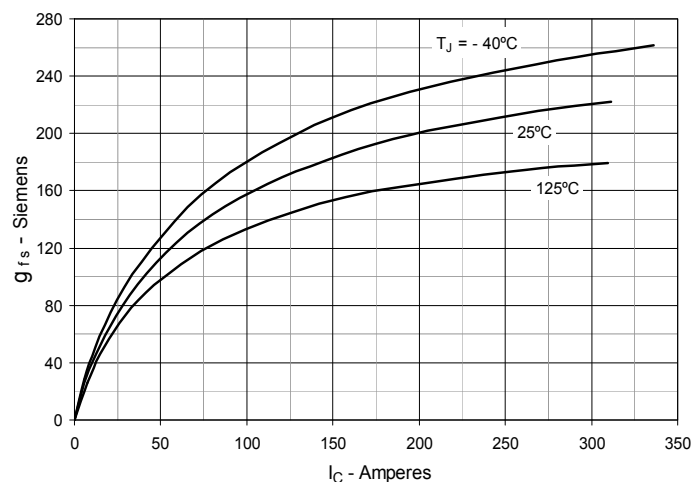


Fig. 7. Gate Charge

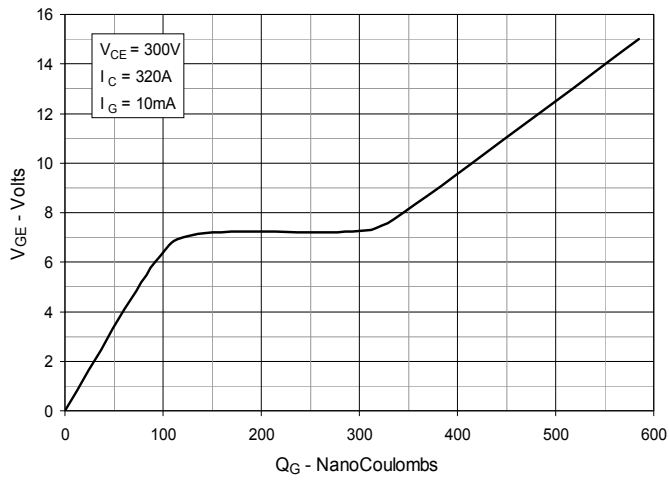


Fig. 8. Capacitance

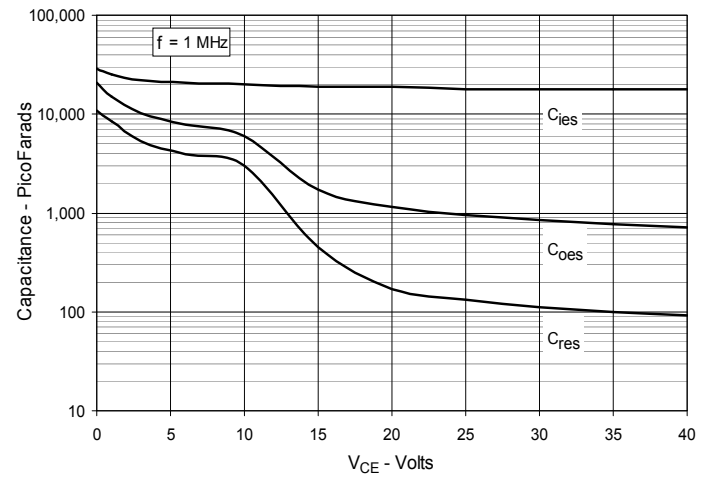


Fig. 9. Reverse-Bias Safe Operating Area

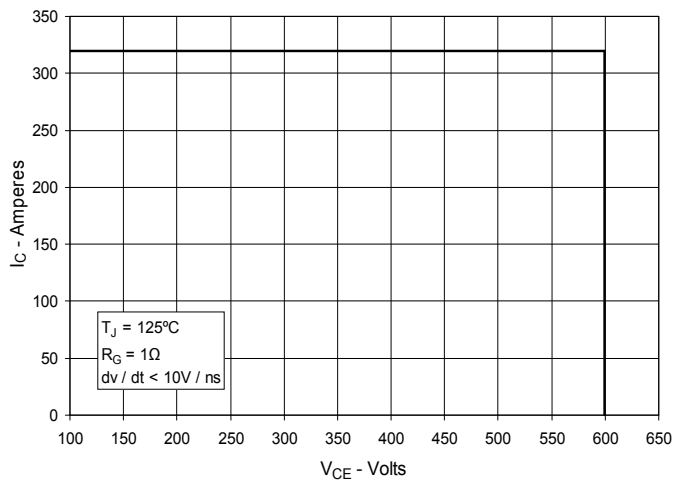
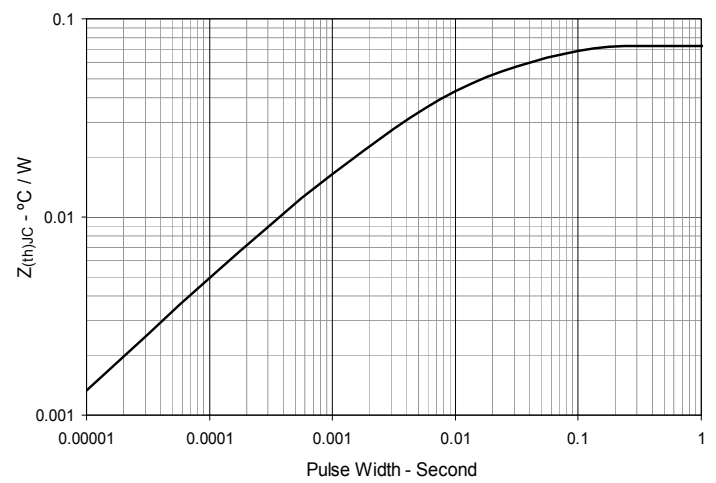
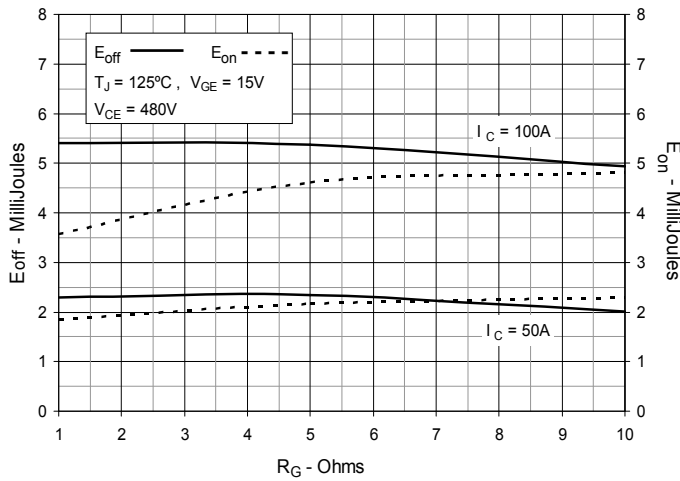


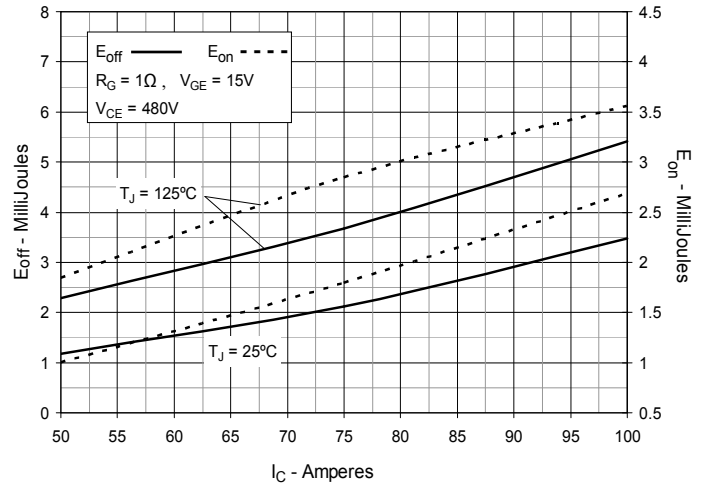
Fig. 10. Maximum Transient Thermal Impedance



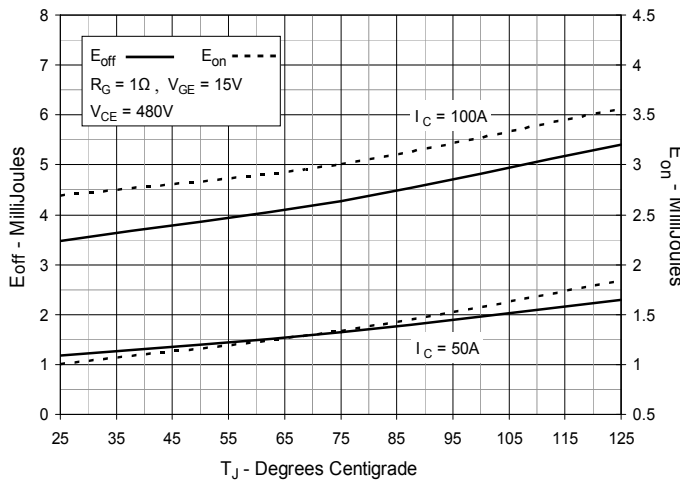
**Fig. 11. Inductive Switching
Energy Loss vs. Gate Resistance**



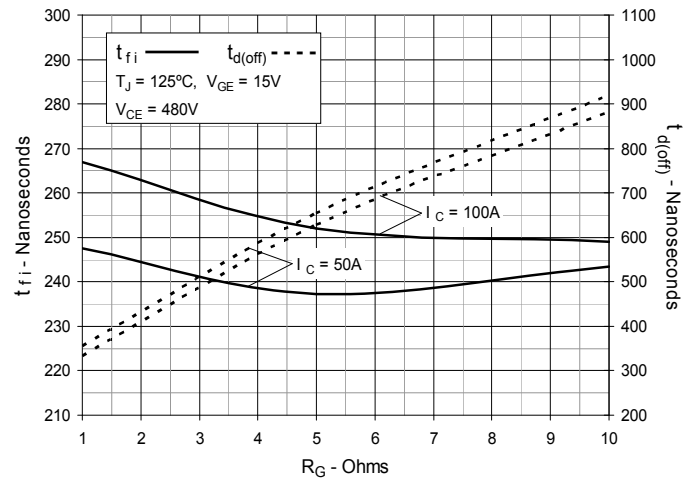
**Fig. 12. Inductive Switching
Energy Loss vs. Collector Current**



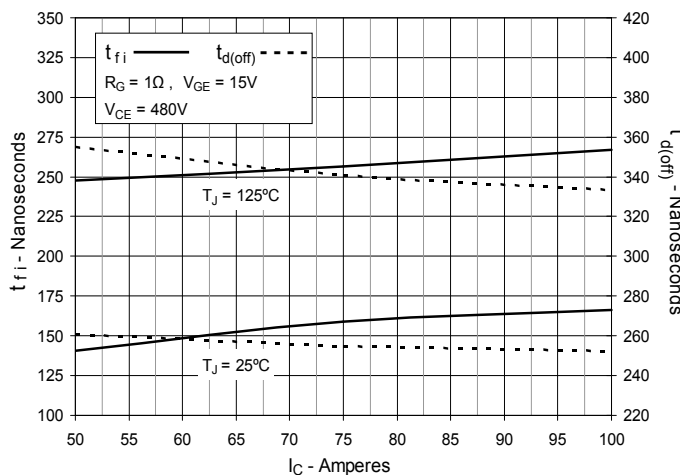
**Fig. 13. Inductive Switching
Energy Loss vs. Junction Temperature**



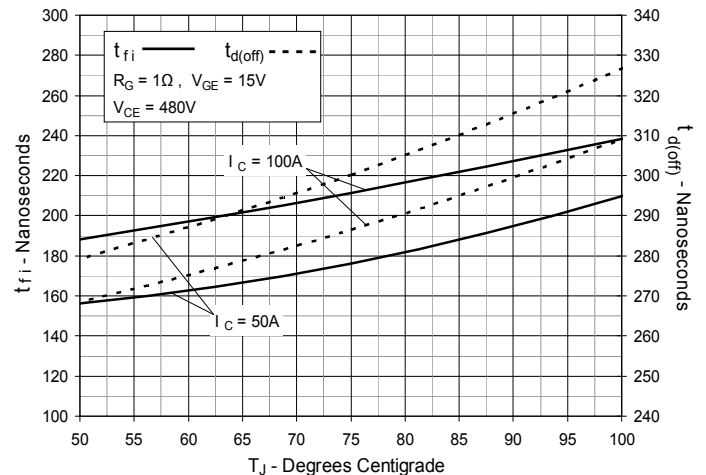
**Fig. 14. Inductive Turn-off
Switching Times vs. Gate Resistance**



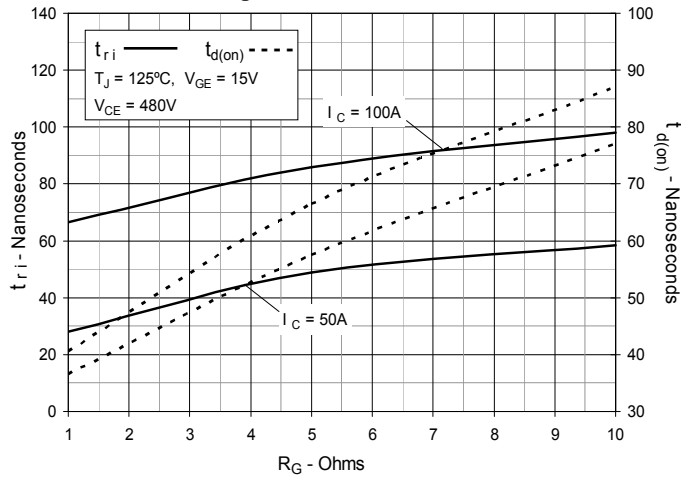
**Fig. 15. Inductive Turn-off
Switching Times vs. Collector Current**



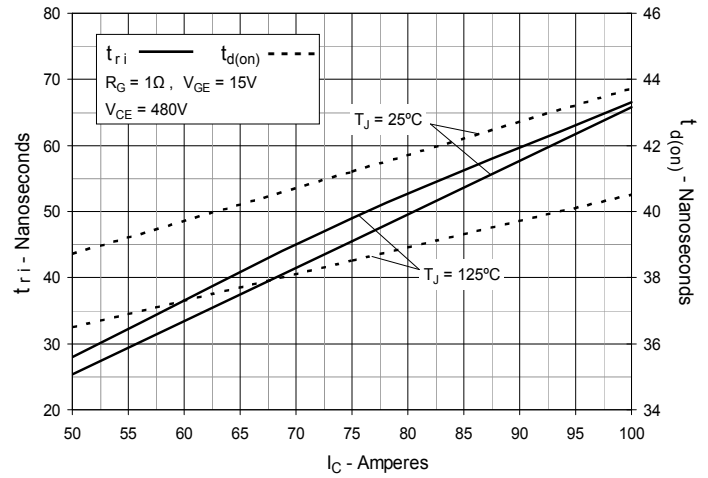
**Fig. 16. Inductive Turn-off
Switching Times vs. Junction Temperature**



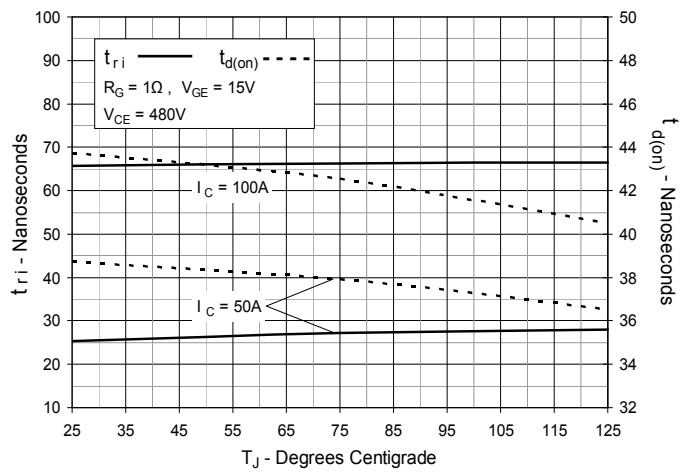
**Fig. 17. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 18. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 19. Inductive Turn-on
Switching Times vs. Junction Temperature**



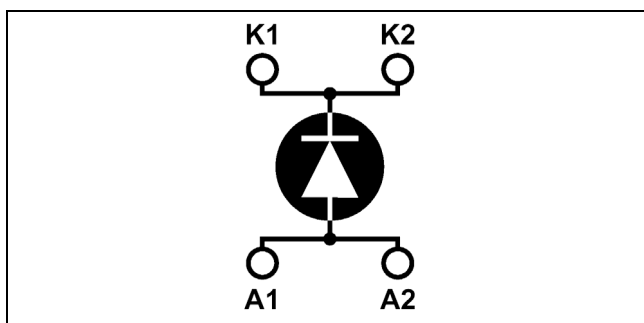


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Single diode Power Module

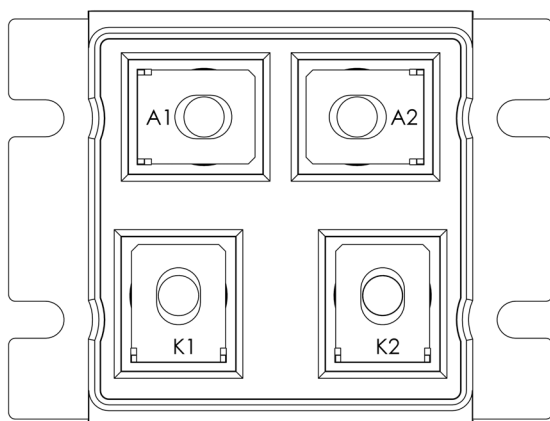
$$V_{CES} = 1200V$$

$$I_C = 400A @ T_c = 80^{\circ}C$$



Application

- Anti-Parallel diode
 - Switchmode Power Supply
 - Inverters
- Snubber diode
- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers
- Electric vehicles



Features

- Ultra fast recovery times
- Soft recovery characteristics
- Very low stray inductance
- High blocking voltage
- High current
- Low leakage current

Benefits

- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>			<i>Max ratings</i>	<i>Unit</i>
V _R	Maximum DC reverse Voltage			1200	V
V _{RRM}	Maximum Peak Repetitive Reverse Voltage				
I _{F(AV)}	Maximum Average Forward Current	Duty cycle = 50%	T _c = 25°C	450	A
			T _c = 80°C	400	
I _{F(RMS)}	RMS Forward Current		750		
I _{FSM}	Non-Repetitive Forward Surge Current		T _j = 25°C	5000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 500A$			2.5	V
		$I_F = 1000A$		2.5		
		$I_F = 500A$ $T_j = 150^{\circ}C$			2.0	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^{\circ}C$		2500	μA
			$T_j = 125^{\circ}C$		5000	
C_T	Junction Capacitance	$V_R = 200V$		600		pF

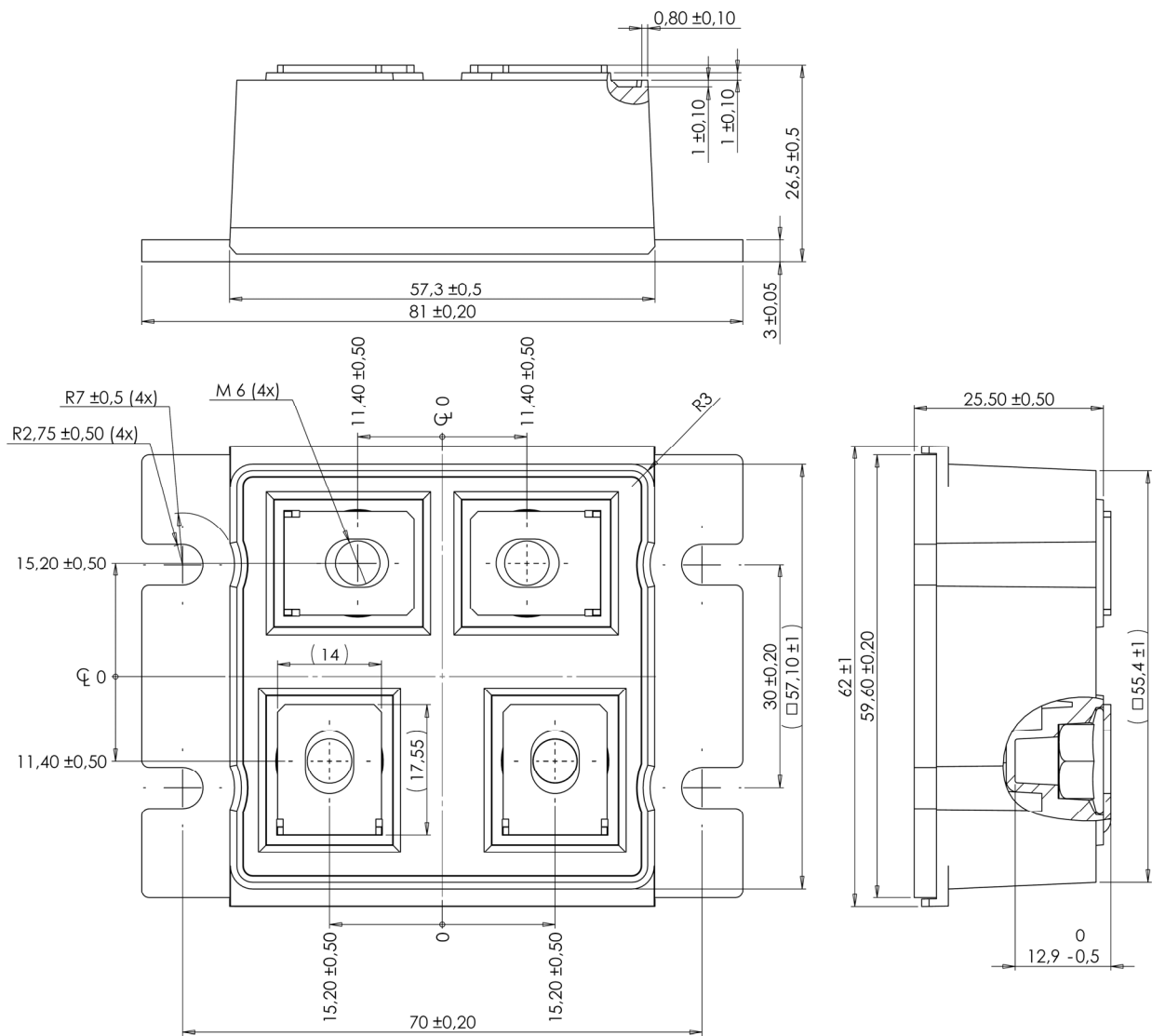
Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
t _{rr1}	Reverse Recovery Time	I _F =1A, V _R =30V di/dt= 15A/μs	T _j = 25°C		90		ns
t _{rr2}		I _F = 500A V _R = 650V	T _j = 25°C		110		
t _{rr3}		di/dt=1000A/μs	T _j = 100°C		175		
t _{fr1}	Forward Recovery Time	I _F = 500A V _R = 650V di/dt=1000A/μs	T _j = 25°C		220		ns
t _{fr2}			T _j = 100°C		220		
I _{RRM1}	Reverse Recovery Current		T _j = 25°C		70		A
I _{RRM2}			T _j = 100°C		120		
Q _{rr1}	Reverse Recovery Charge		T _j = 25°C		10		μC
Q _{rr2}			T _j = 100°C		30		
V _{fr1}	Forward Recovery Voltage		T _j = 25°C		26		V
V _{fr2}			T _j = 100°C		26		
d _{IM} /dt	Rate of Fall of Recovery Current		T _j = 25°C		1200		A/μs
			T _j = 100°C		800		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance			0.08	$^{\circ}C/W$
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, 50/60Hz	4000			V
T_J	Operating junction temperature range	-40		150	$^{\circ}C$
T_{STG}	Storage Temperature Range	-40		125	
T_C	Operating Case Temperature	-40		100	
Torque	Mounting torque	To heatsink M5	2.5	3.5	N.m
		For terminals M6	3	4	
Wt	Package Weight			250	g

LP4 Package outline (dimensions in mm)



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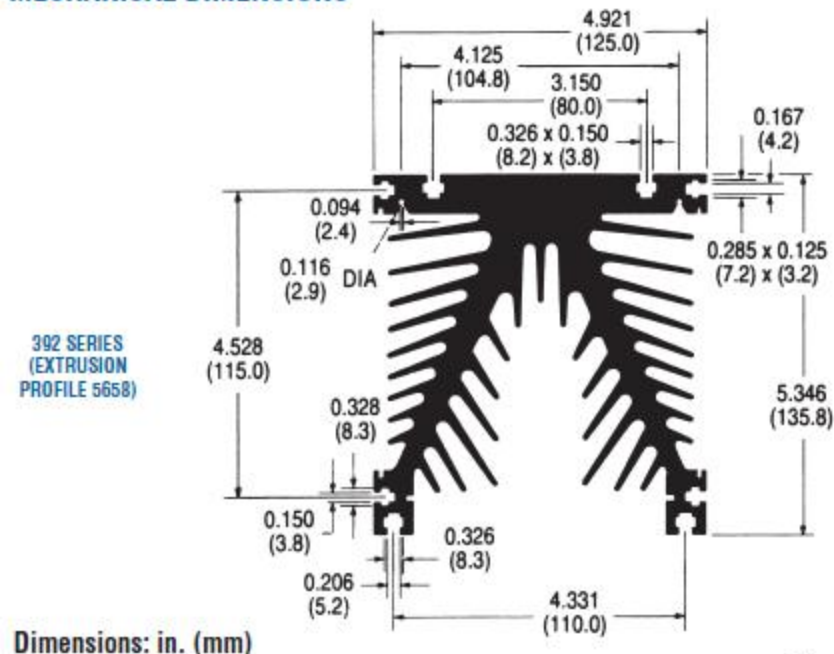
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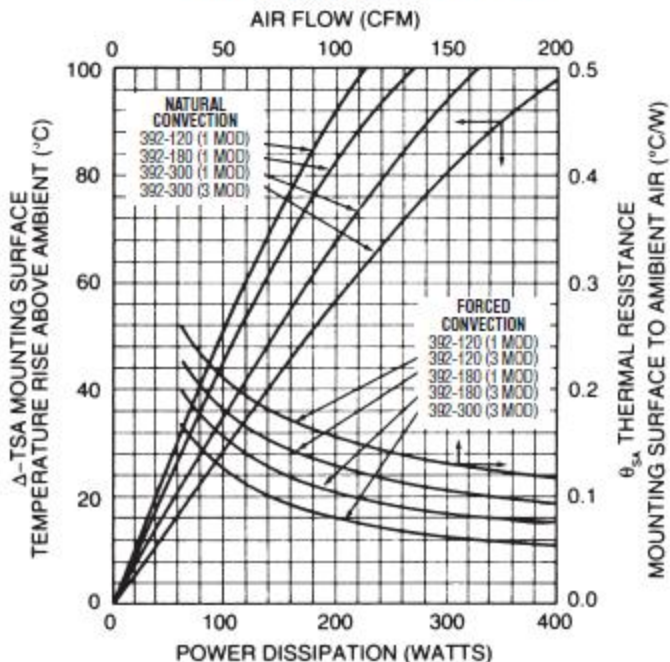
wakefield-vette

Standard P/N, Finish		Length in. (mm)	Thermal Resistance at Typical Load		Weight lbs. (grams)
Black Anodized	Gold Iridite		Natural Convection (θ_{sa}) (°CW)	Forced Convection (θ_{sa}) (°CW)	
392-120AB	392-120AG	4.725 (120.0)	0.50	0.16 @ 100 CFM	4.452 (2019.43)
392-180AB	392-180AG	7.087 (180.0)	0.43	0.11 @ 100 CFM	6.636 (3010.09)
392-300AB	392-300AG	11.811 (300.0)	0.33	0.08 @ 100 CFM	10.420 (4726.51)

MECHANICAL DIMENSIONS



NATURAL AND FORCED CONVECTION CHARACTERISTICS



FEATURES AND BENEFITS*

- Up to 1,000,000 duty cycles or 10 year DC life
- 48V DC working voltage
- Active cell balancing
- Temperature output
- Overvoltage outputs available
- High power density
- Extreme Vibration Environment Compatible

TYPICAL APPLICATIONS

- Hybrid vehicles
- Rail
- Heavy industrial equipment
- UPS systems



PRODUCT SPECIFICATIONS

ELECTRICAL

BMOD0165 P048 C01

Rated Capacitance ¹	165 F
Minimum Capacitance, initial ¹	165 F
Maximum Capacitance, initial ¹	198 F
Maximum ESR _{DC} , initial ¹	6.0 mΩ
Test Current for Capacitance and ESR _{DC} ¹	100 A
Rated Voltage	48 V
Stored Energy ⁴	53 Wh
Absolute Maximum Voltage ²	51 V
Absolute Maximum Current	1,900 A
Maximum Series Voltage	750 V
Capacitance of Individual Cells ⁸	3,000 F
Stored Energy, Individual Cell ⁸	3.0 Wh
Number of Cells	18

TEMPERATURE

Operating Temperature (Cell Case Temperature)	
Minimum	-40°C
Maximum	65°C
Storage Temperature (Stored Uncharged)	
Minimum	-40°C
Maximum	70°C

*Results may vary. Additional terms and conditions, including the limited warranty, apply at the time of purchase. See the warranty details for applicable operating and use requirements.

PRODUCT SPECIFICATIONS (Cont'd)**PHYSICAL****BMOD0165 P048 C01**

Mass, typical	14.2 kg
Power Terminals	M8/M10
Recommended Torque - Terminal	20 Nm (M8)/30 Nm (M10)
Vibration Specification	ISO 16750-3, Table 12
Shock Specification	IEC 60068-2-27, -29
Environmental Protection	IP65
Cooling	Natural Convection

MONITORING / CELL VOLTAGE MANAGEMENT

Internal Temperature Sensor ³	NTC Thermistor (10 kΩ)
Temperature Interface	Analog
Cell Voltage Monitoring ³	Overvoltage Alarm (open collector)
Connector (Mating)	Deutsch DTM04-4P, Amphenol ATM04-4P
Cell Management System	CMS 2.0

SAFETY

Short Circuit Current, typical (Current possible with short circuit from rated voltage. Do not use as an operating current.)	8,100 A
Certifications	RoHS, UL810a (50 volts)
High-Pot Test ⁹	2,750 VDC

TYPICAL CHARACTERISTICS

THERMAL CHARACTERISTICS

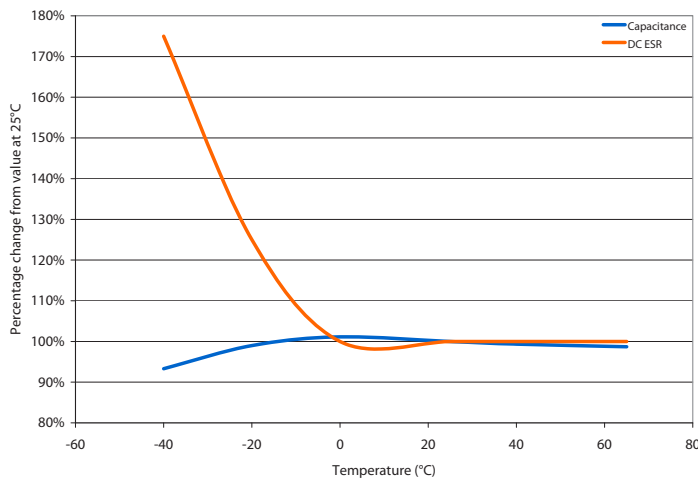
BMOD0165 P048 C01

Thermal Resistance (R_{ca} , All Cell Cases to Ambient), typical ⁵	0.40°C/W
Thermal Capacitance (C_{th}), typical	13,000 J/°C
Maximum Continuous Current ($\Delta T = 15\text{ °C}$) ⁵ (BOL, Beginning of Life)	79 A, RMS
Maximum Continuous Current ($\Delta T = 40\text{ °C}$) ⁵ (BOL, Beginning of Life)	130 A, RMS

LIFE

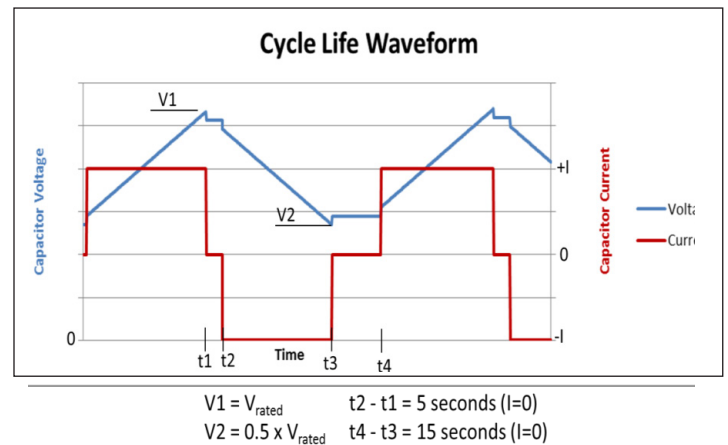
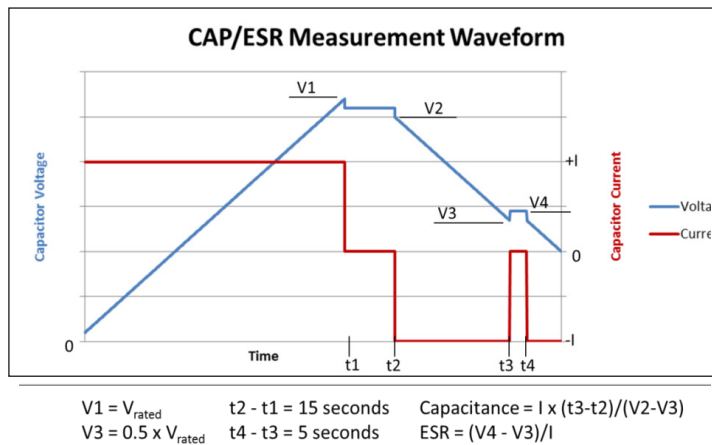
DC Life at High Temperature ¹ (held continuously at Rated Voltage and Maximum Operating Temperature)	1,500 hours
Capacitance Change (% decrease from minimum initial value)	20%
ESR Change (% increase from maximum initial value)	100%
Projected DC Life at 25°C ¹ (held continuously at Rated Voltage)	10 years
Capacitance Change (% decrease from minimum initial value)	20%
ESR Change (% increase from maximum initial value)	100%
Projected Cycle Life at 25°C ^{1,6,7}	1,000,000 cycles
Capacitance Change (% decrease from minimum initial value)	20%
ESR Change (% increase from maximum initial value)	100%
Test Current	100 A
Shelf Life (Stored uncharged at 25°C)	4 years

ESR AND CAPACITANCE VS TEMPERATURE



NOTES

1. Capacitance and ESR_{DC} measured at 25°C using specified test current per waveform below.
2. Absolute maximum voltage, non-repeated. Not to exceed 1 second.
3. Please refer to module user manual for additional technical details.
4. $E_{\text{stored}} = \frac{1}{2} \frac{CV^2}{3,600}$
5. $\Delta T = I_{\text{RMS}}^2 \times ESR \times R_{ca}$
6. Cycle using specified test current per waveform below.
7. Cycle life varies depending upon application-specific characteristics. Actual results will vary.
8. Per United Nations material classification UN3499, all Maxwell ultracapacitors have less than 10 Wh capacity to meet the requirements of Special Provisions 361. Both individual ultracapacitors and modules composed of those ultracapacitors shipped by Maxwell can be transported without being treated as dangerous goods (hazardous materials) under transportation regulations.
9. Duration = 60 seconds. Not intended as an operating parameter.



Top View Dimensions:

- Overall Length (L): 344±1
- Overall Width (W): 121.2±1
- Distance from top edge to top terminal: 174.2±1
- Distance from left edge to left terminal: 122.5±1.2
- Distance between terminals: 64.6±1
- Distance from bottom edge to bottom terminal: 170±0.25
- Distance from right edge to right terminal: 34.4±1.2
- Distance from top edge to top terminal (alternative): 141.8±1
- Distance from bottom edge to bottom terminal (alternative): 49.4±1
- Distance between terminals (alternative): 396.2±0.25

Labels and Features:

- Maxwell Technologies logo
- WARNING label
- VENT label
- TERMINAL SCREWS REMOVED FOR CLARITY
- 4X Ø9.5^{+0.3}_{-0.8} THRU
- M8 X 1.25 POSITIVE TERMINAL THREAD DEPTH: 20-22mm MAX TORQUE 20 N-m
- M10 TERMINAL SCREW
- MONITOR CABLE
- M8 TERMINAL SCREW
- CUSTOMER MATING CONNECTOR: DEUTSCH DTMO44P OR AMPHENOL ATM04-4P
- 116 FLAT SURFACE
- 92 FLAT SURFACE

Side View Dimensions:

- Height (H1): 49±5
- Height (H2): 360±25

Product dimensions are for reference only unless otherwise identified. Product dimensions and specifications may change without notice. Please contact Maxwell Technologies directly for any technical specifications critical to application. All products featured on this datasheet are covered by the following U.S. patents and their respective foreign counterparts: 6643119, 7180726, 7295423, 7342770, 7352558, 7384433, 7440258, 7492571, 7508651, 7580243, 7791860, 7816891, 7859826, 7883553, 7935155, 8072734, 8098481, 8279580, and patents pending.



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